



30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UX)

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C	
001/	20mΩ @ V _{GS} = -10V	004	
-30V	29mΩ @ V _{GS} = -5V	-30A	

Features

- Low RDS(ON) Ensures On-State Losses Are Minimized
- Small Form-Factor, Thermally Efficient Package Enables Higher **Density End Products**
- Occupies Just 33% of The Board Area Occupied by SO-8, **Enabling Smaller End Product**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES™ DMP3036SFVQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions

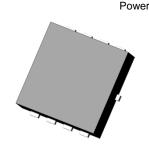
Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

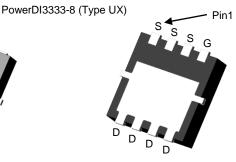
- General-purpose interfacing switches
- Power management functions

Mechanical Data

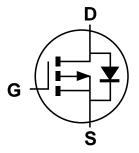
- Package: PowerDI®3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.03 grams (Approximate)







Bottom View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Package	Packing		
Fait Number	rackage	Qty.	Carrier	
DMP3036SFVQ-7	PowerDI3333-8 (Type UX)	2,000	Tape & Reel	
DMP3036SFVQ-13	PowerDI3333-8 (Type UX)	3,000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



36F = Product Type Marking Code YYWW = Date Code Marking \overline{YY} = Last Two Digits of Year (ex: 22 = 2022) WW = Week Code (01 to 53)



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	-30	V	
Gate-Source Voltage		Vgss	±25	V
Continuous Drain Current, $V_{GS} = -10V$ (Note 6) $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		lD	-8.7 -7.0	А
Continuous Drain Current, $V_{GS} = -10V$ (Note 7) $ T_C = +25^{\circ}C $ $ T_C = +70^{\circ}C $		lD	-30 -25	А
Maximum Continuous Body Diode Forward Current (Note 7)	ls	-3.6	А	
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	IDM	-80	Α	
Avalanche Current, L = 0.3mH (Note 8)	las	-17.5	Α	
Avalanche Energy, L = 0.3mH (Note 8)	Eas	64	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	137	°C/W
Total Power Dissipation (Note 6)	PD	2.3	W	
Thermal Resistance, Junction to Ambient (Note 6) Steady State		RθJA	55	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _θ JC	3.5	C/VV
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30		_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	1	-1	μA	$V_{DS} = -30V$, $V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	1	-2.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		_		20	mΩ	Vgs = -10V, ID = -8A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	29		$V_{GS} = -5V, I_D = -5A$	
Diode Forward Voltage	VsD		-0.7	-1.2	V	Vgs = 0V, Is = -1A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	1	1931	1		V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	226		pF		
Reverse Transfer Capacitance	Crss	_	168	_			
Gate Resistance	Rg	_	11	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Total Gate Charge (VGS = -5V)	Qg	_	8.8	_			
Total Gate Charge (V _{GS} = -10V)	Qg	_	16.5	_	~C	V _{DS} = -15V, I _D = -10A	
Gate-Source Charge	Qgs	_	2.6	_	nC		
Gate-Drain Charge	Q _{gd}	_	3.6	_			
Turn-On Delay Time	t _{D(on)}	_	8.2	_		$V_{DD} = -15V$, $V_{GS} = -10V$, $R_{GEN} = 3\Omega$, $I_{D} = -10A$	
Turn-On Rise Time	tR	_	14	_			
Turn-Off Delay Time	t _{D(off)}	_	65	_	ns		
Turn-Off Fall Time	tF	_	31.6	_			
Reverse Recovery Time	trr	_	9.3	_	ns	0.0 41/44 500.0 ///-	
Reverse Recovery Charge	Qrr	_	12.2	_	$_{\text{nC}}$ I _F = -8A, di/dt = 500A/µs		

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

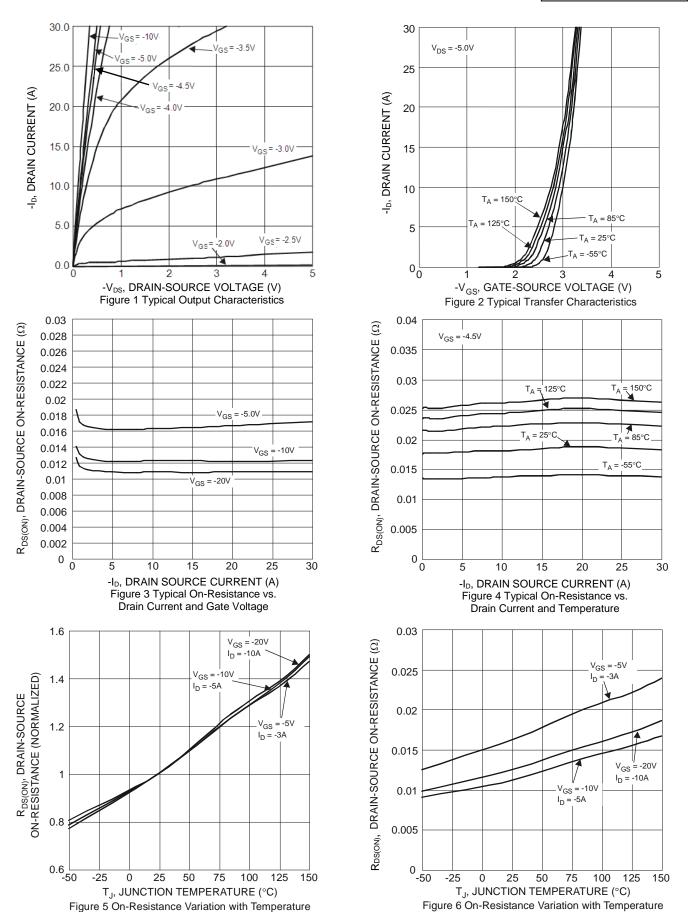
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).

8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_{J} = +25^{\circ}C$.

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.







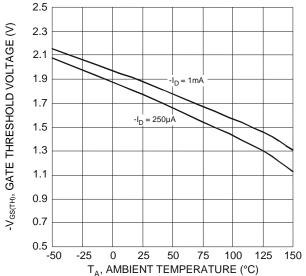


Figure 7 Gate Threshold Variation vs. Ambient Temperature

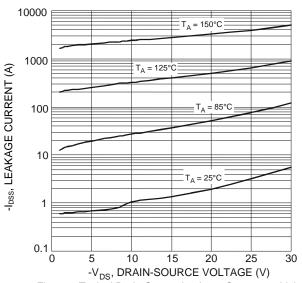
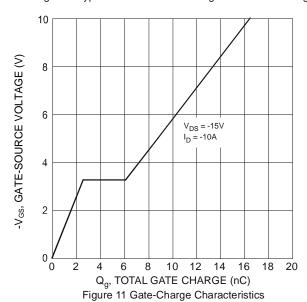


Figure 9 Typical Drain-Source Leakage Current vs. Voltage



30 $V_{GS} = 0V$ 25 -Is, SOURCE CURRENT (A) 20 15 T_A= 150°C 10 _= 25°C 5 0 _ 0.3 1.2 0.9 1.5 -V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 8 Diode Forward Voltage vs. Current

10000 C_{iss}

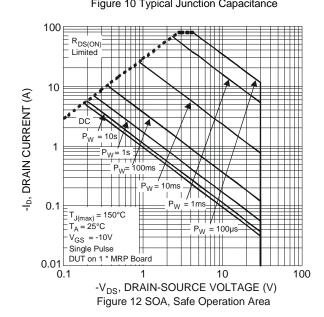
1000 C_{iss}

1000 C_{rss}

100 C_{oss}

100 C_{oss}

100 DAIN-SOURCE VOLTAGE (V)
Figure 10 Typical Junction Capacitance





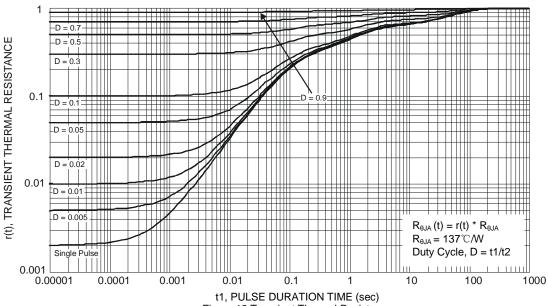


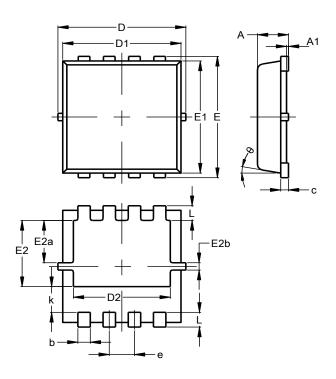
Figure 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)

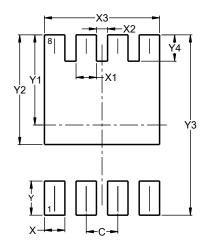


	PowerDI3333-8 (Type UX)				
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	1		
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E2a	0.95	1.35	1.15		
E2b	0.10	0.30	0.20		
е	0.65 BSC				
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		



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